Abstracts

GaAs and InP-Based Monolithically Integrated Transmitters and Photoreceivers

---

P. Bhattacharya. "GaAs and InP-Based Monolithically Integrated Transmitters and Photoreceivers." 1994 MTT-S International Microwave Symposium Digest 94.3 (1994 Vol. III [MWSYM]): 1491-1492.

High-performance GaAs and InP-based components are required for the development long- and short -distance communication links. Our work in the development of monolithically integrated transmitters and photoreceivers will be described, with reference to ongoing work elsewhere. Challenges in terms of materials incompatibility and device design and intrinsic and extrinsic limits of device and circuit performance will be discussed.

❑ Return to main document.

Click on title for a complete paper.